

isc Silicon NPN Darlington Power Transistor

BDW93C

DESCRIPTION

- With TO-220 packaging
- Very high DC current gain
- Monolithic darlington transistor with integrated antiparallel collector-emitter diode
- Complement to Type BDW94C
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

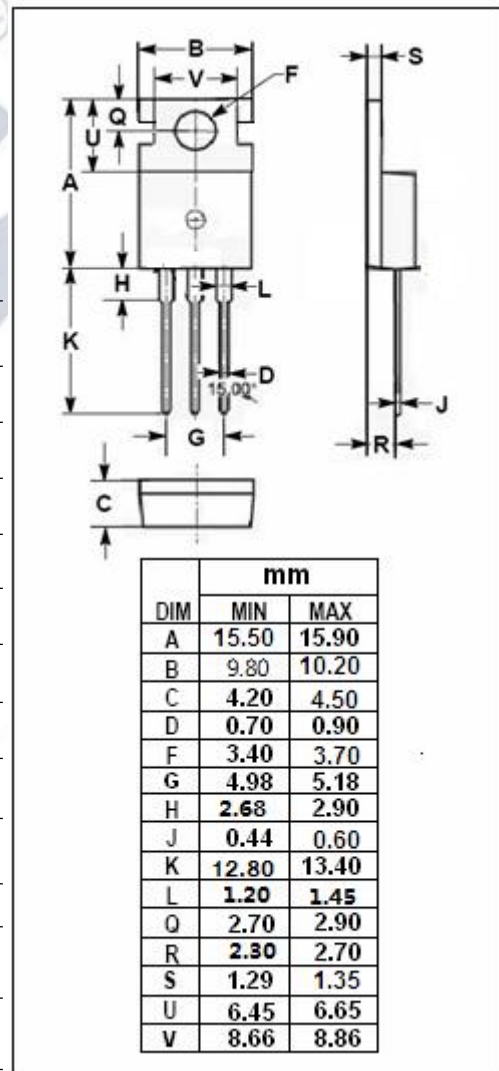
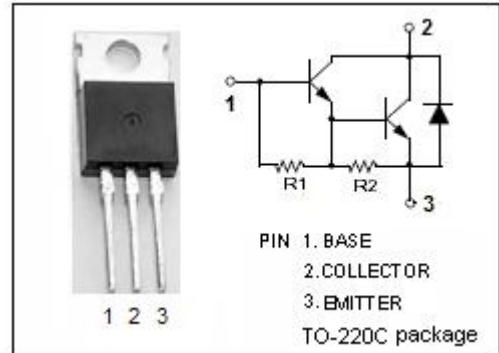
- AC-DC motor control
- Electronic ignition
- Alternator regulator

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	12	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current- Continuous	0.2	A
P_C	Collector Power Dissipation	80	W
T_j	Max.Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-65~150	$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance,Junction to Case	1.56	$^{\circ}\text{C/W}$



isc Silicon NPN Darlington Power Transistor**BDW93C****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 100mA, I _B = 0	100		V
V _{CE(sat)1}	Collector-Emitter Saturation Voltage	I _C = 5A ,I _B = 20mA		2.0	V
V _{CE(sat)2}	Collector-Emitter Saturation Voltage	I _C = 10A ,I _B = 100mA		3.0	V
V _{BE(sat)1}	Base-Emitter Saturation Voltage	I _C = 5A ,I _B = 20mA		2.5	V
V _{BE(sat)2}	Base-Emitter Saturation Voltage	I _C = 10A ,I _B = 100mA		4.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} =100V, I _E = 0		100	μ A
I _{CEO}	Collector Cutoff Current	V _{CE} = 100V, I _B = 0		1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0		2	mA
h _{FE-1}	DC Current Gain	I _C = 3A ; V _{CE} = 3V	1000	20000	
h _{FE-2}	DC Current Gain	I _C = 5A ; V _{CE} = 3V	750	20000	
h _{FE-3}	DC Current Gain	I _C = 10A ; V _{CE} = 3V	100	20000	